

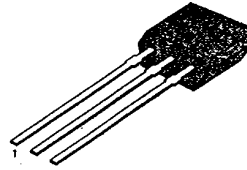
KSC3488**NPN EPITAXIAL SILICON TRANSISTOR****LOW FREQUENCY POWER AMPLIFIER**

- Complement to KSA1378
- Collector Dissipation $P_C = 300\text{mW}$

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	30	V
Collector-Emitter Voltage	V_{CE0}	25	V
Emitter-Base Voltage	V_{EB0}	5	V
Collector Current	I_C	300	mA
Collector Dissipation	P_C	300	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 - 150	$^\circ\text{C}$

TO-92S



1. Emitter 2. Collector 3. Base

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CB0}	$I_C = 100\mu\text{A}, I_E = 0$	30			V
Collector-Emitter Breakdown Voltage	BV_{CE0}	$I_C = 10\text{mA}, I_B = 0$	25			V
Emitter-Base Breakdown Voltage	BV_{EB0}	$I_E = -10\mu\text{A}, I_C = 0$	5			V
Collector Cut-off Current	I_{CB0}	$V_{CB} = 25\text{V}, I_E = 0$			0.1	μA
Emitter Cut-off Current	I_{EB0}	$V_{EB} = 3\text{V}, I_C = 0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = 1\text{V}, I_C = 50\text{mA}$	70		400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 300\text{mA}, I_B = 30\text{mA}$		0.14	0.4	V

 h_{FE} CLASSIFICATION

Classification	O	Y	G
h_{FE}	70-140	120-240	200-400

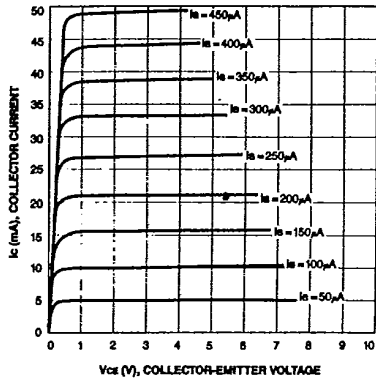


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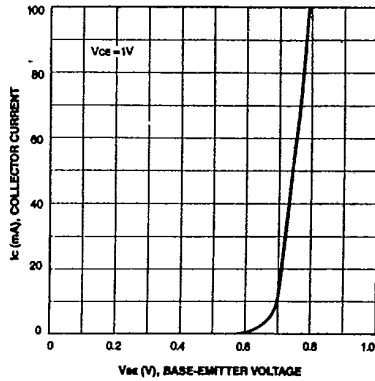
NPN EPITAXIAL SILICON TRANSISTOR

T-29-17

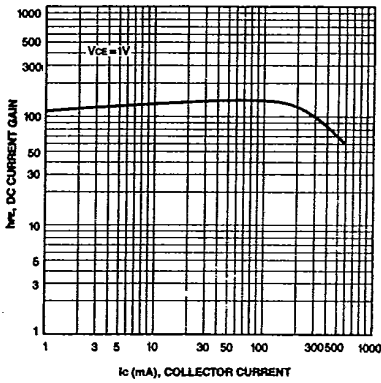
STATIC CHARACTERISTIC



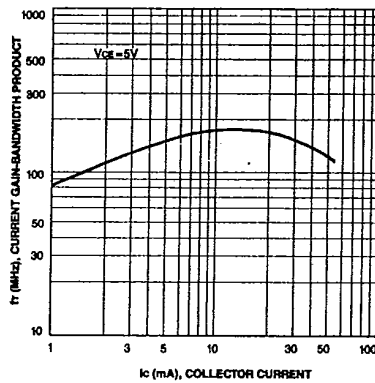
BASE-EMITTER ON VOLTAGE



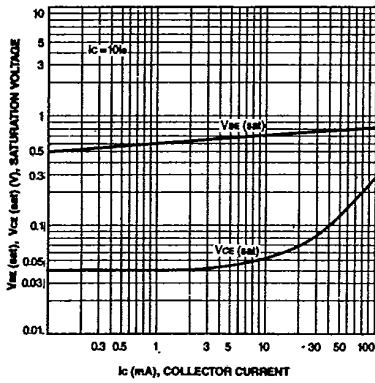
DC CURRENT GAIN



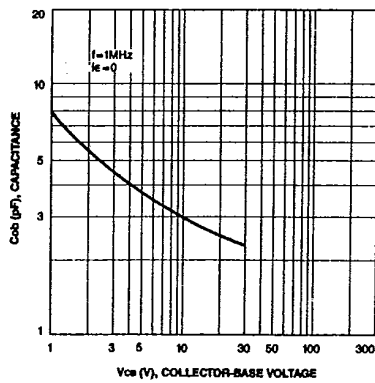
CURRENT GAIN-BANDWIDTH PRODUCT



BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



COLLECTOR OUTPUT CAPACITANCE



3